(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
4 March 2004 (04.03.2004)

PCT

(10) International Publication Number
WO 2004/019404 A3

(51) International Patent Classification[7]: H01L 21/762

(21) International Application Number:
PCT/IB2003/004143

(22) International Filing Date: 26 August 2003 (26.08.2003)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:

0210587	26 August 2002 (26.08.2002)	FR
60/431,928	9 December 2002 (09.12.2002)	US

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(81) Designated States *(national)*: CN, JP, KR, SG, US.

(84) Designated States *(regional)*: European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR).

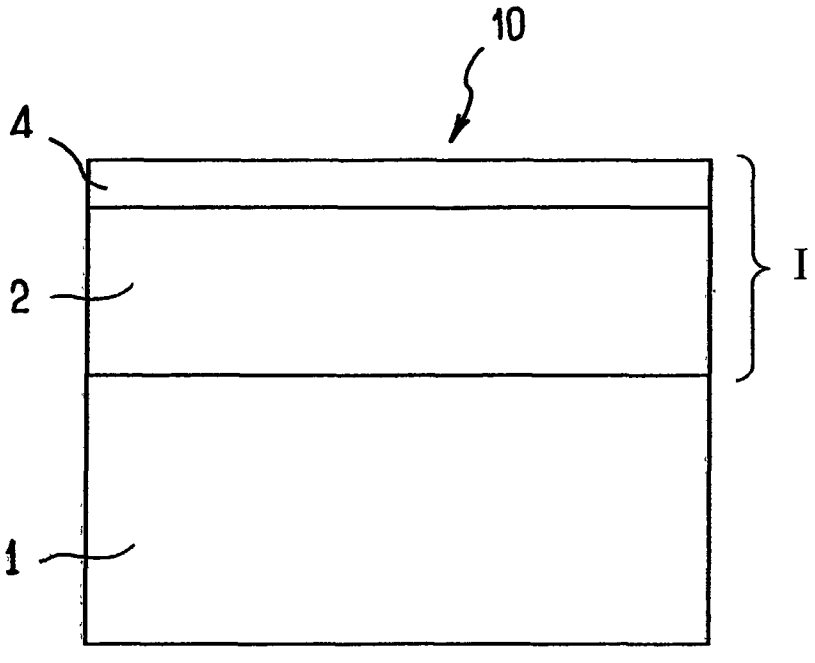
Declaration under Rule 4.17:
— *of inventorship (Rule 4.17(iv)) for US only*

Published:
— *with international search report*
— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*

(88) Date of publication of the international search report:
12 August 2004

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: RECYCLING A WAFER COMPRISING A BUFFER LAYER, AFTER HAVING TAKEN OFF A THIN LAYER THEREFROM



(57) Abstract: Method of recycling a donor wafer (10) after taking off at least one useful layer, the donor wafer (10) comprising successively a substrate (1), a buffer structure (1) and, before taking-off, a useful layer. The method comprises removal of substance relating to part of the donor wafer (10) on the side where the taking-off took place, such that, after removal of substance, there remains at least part of the buffer structure (1) capable of being reused as at least part of a buffer structure (1) during a subsequent taking-off of a useful layer. The present document also relates to: - a method of producing a donor wafer (10) which can be recycled according to the invention; - methods of taking a thin layer off a donor wafer (10) which can be recycled according to the invention; - donor wafers (10) which can be recycled according to the invention.

WO 2004/019404 A3